

L Number	Hits	Search Text	DB	Time stamp
1	1	("20010053589").PN.	US-PGPUB	2004/01/14 06:50
-	855	high adj voltage adj semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/17 10:45
-	97	(257/168).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/17 10:53
-	708	(257/409).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 14:37
-	18	(high adj voltage adj semiconductor) same (edg\$3 adj (structure or device))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/13 14:15
-	1	("20020005733").PN.	US-PGPUB	2004/01/14 06:50
-	5	((("6081009") or ("5438215") or ("6566709") or ("6498367") or ("5594261"))).PN.	USPAT	2004/01/13 14:28
-	6	((("6081009") or ("5438215") or ("6566709") or ("6498367") or ("5594261") or ("5886383"))).PN.	USPAT	2003/06/17 10:49
-	11	((("6081009") or ("5438215") or ("6566709") or ("6498367") or ("5594261") or ("5886383") or ("5396085") or ("5416354") or ("5719411") or ("5818084") or ("5877515"))).PN.	USPAT	2003/06/17 10:49
-	672	(257/341).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/17 10:53
-	209	(257/495).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/17 10:53
-	402	(257/653).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/17 10:53
-	1188	(257/401).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/17 10:54
-	359	(257/342).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/17 10:54
-	345	(257/139).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/17 10:54
-	284	(257/133).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/17 10:54

-	103	(257/149).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:54
-	351	(257/147).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:54
-	175	(257/155).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:54
-	1257	(257/355).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:55
-	104	(257/135).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:55
-	101	(257/168).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:55
-	725	(257/409).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:55
-	1531	257/168,409,341,495,653,401,342,139,133,149, and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))	USPAT;155,355, US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 11:07
-	1184	(257/168,409,341,495,653,401,342,139,133,149 and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))) and @ad<=19981209	USPAT;155,355, US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 14:38
-	28	((257/168,409,341,495,653,401,342,139,133,149 and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))) and @ad<=19981209) and (edg\$4 adj (structures or device))	USPAT;155,355, US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 11:11
-	2	((("5719411") or ("6225165"))).PN.	USPAT	2003/06/30 10:03
-	2	((("6522164") or ("6300171"))).PN.	USPAT	2004/01/13 14:28
-	1186	(257/168,409,341,495,653,401,342,139,133,149 and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))) and @ad<=19981209	USPAT;155,355, US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 14:38
-	11497	(257/\$.ccls. and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))) and @ad<=19981209	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 14:40
-	3	(257/\$.ccls. and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))) and @ad<=19981209 and (high adj voltage adj semiconductor) same (edg\$3 adj (structure or device))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 14:40

-	3	(257/\$.ccls. and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))) and (high adj voltage adj semiconductor) same (edg\$3 adj (structure or device)) and @ad<=19981209	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 14:40
-	5	(257/\$.ccls. and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))) and (high adj voltage adj semiconductor) and (edg\$3 adj (structure or device)) and @ad<=19981209	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 14:59
-	3	(257/\$.ccls. and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))) and @ad<=19981209 and ((high adj voltage adj semiconductor) same (edg\$3 adj (structure or device)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 14:47
-	8	438/\$.ccls. and ((high adj voltage) same (edg\$3 adj (structure or device))) and @ad<=19981209	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 15:02
-	28	257/\$.ccls. and ((high adj voltage) same (edg\$3 adj (structure or device))) and @ad<=19981209	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 15:03
-	40	438/\$.ccls. and (high adj voltage) and (edg\$3 adj (structure or device)) and @ad<=19981209	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 15:11
-	134	257/\$.ccls. and (high adj voltage) and (edg\$3 adj (structure or device)) and @ad<=19981209	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/13 15:11